



IGBT Chip

Die In Wafer Form

1200V IC (nom) =50A Vce(sat)typ=3.5V@IC(nom)@25°C UltraFast IGBT ShortCircuit Rated 150mm Wafer
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Applications

Welding Machine/ Cutting Machine/HF Power

Features

Non Punch Through (NPT) Technology
 Low Vce(sat)
 10µs Short Circuit Capability
 Square RBSOA
 Positive Vce(sat) Temperature Coefficient

Chip Type	ICn	Vce	Die size	Wafer size
SYC50PN120WHF	50A	1200V	7.75*9.91 mm ²	6 inch

Mechanical Parameters

Die size	7.75mm*9.91mm
Emitter pad size	See chip drawing
Gate pad size	0.909mm*0.925mm
Area total	53.50mm ²
Silicon thickness	180um
Wafer size	150mm
Maximum possible chips per wafer	154pcs
Passivation frontside	Polyimide
Pad metal	4000nm AlSiCu
Backside metal	Al - Ti - Ni/V - Ag, (1kA - 1kA - 2kA - 8kA) suitable for epoxy and soft solder die bonding
Die bond	Soft solder
Wire bond	Al, ≤500um
Reject ink dot size	∅ 0.65mm; max. 1.2mm
Storage environment (<6 months) for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C
Storage environment (<6 months) for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.

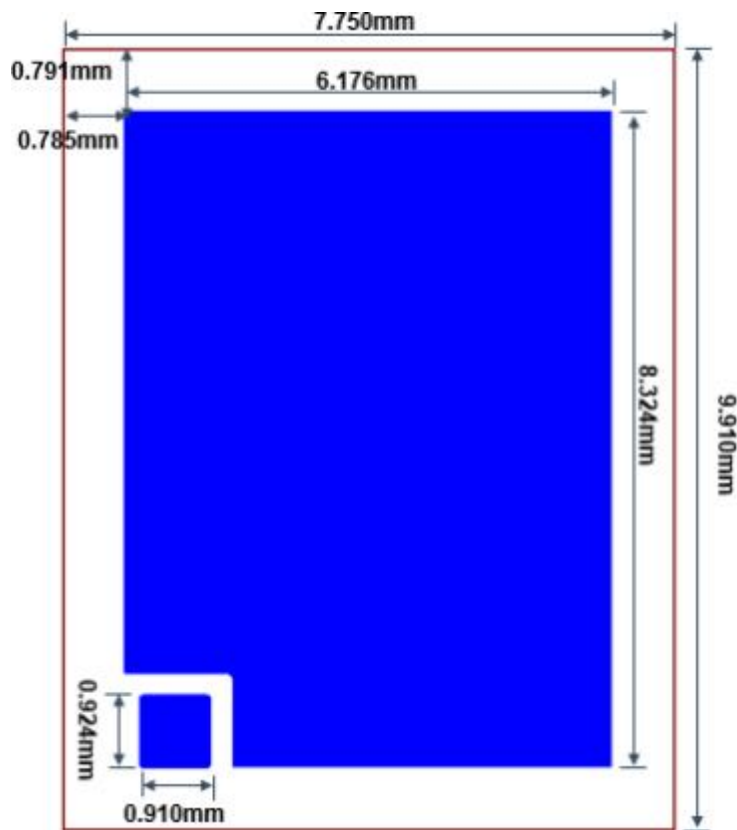
Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj}=25^{\circ}\text{C}$	VCE	1200	V
DC collector current, limited by T_{vj} max 1	IC	50	A
Pulsed collector current, t_p limited by T_{vj} max 2	IC,puls	100	A
Gate- emitter voltage	VGE	± 20	V
Junction temperature	T_{vj}	150	C
Operating junction temperature	T_{vj} op	-40 - 125	C
Short circuit data ^{2 / 3} $V_{GE}=15\text{V}$, $V_{CC}=600\text{V}$, $T_{vj}=150^{\circ}\text{C}$	tsc	10	ps

Static Characteristics (tested on chip)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Collector- emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}$, $I_c=250\mu\text{A}$	1200			V
Collector- emitter saturation voltage	$V_{CE(sat)}$	$I_c=50\text{A}$, $V_{GE}=15\text{V}$, $T_{vj}=25^{\circ}\text{C}$	3.1	3.5	3.9	V
Gate- emitter threshold voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, $I_c=2\text{mA}$, $T_{vj}=25^{\circ}\text{C}$	4.95	5.7	6.1	V
Collector- emitter cut-off current	I_{CES}	$V_{CE}=1200\text{V}$, $V_{GE}=0\text{V}$, $T_{vj}=25^{\circ}\text{C}$			20	μA
Gate- emitter leakage current	I_{GES}	$V_{CE}=0$, $V_{GE}=20\text{V}$, $T_{vj}=25^{\circ}\text{C}$			100	nA

1. Depending on thermal properties of assembly.
2. Not subject or production test - verified by design/characterization.
3. Allowed number of short circuits: <1000; time between short circuit





Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Revision History

Revision	Subjects(major changes since last revision)	Date
1.0	Final date sheet	2019.12.25
1.1	Change specification name and company address	2022.10.27